

V Ramgopal Rao

List of Publications by Year in descending order

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316
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316
times ranked

4295
citing authors

#	ARTICLE	IF	CITATIONS
1	A Tunnel FET for V_{DD} Scaling Below 0.6 V With a CMOS-Comparable Performance. IEEE Transactions on Electron Devices, 2011, 58, 1855-1863.	1.6	144
2	Gate Fringe-Induced Barrier Lowering in Underlap FinFET Structures and Its Optimization. IEEE Electron Device Letters, 2008, 29, 128-130.	2.2	111
3	Polymer nanocomposite nanomechanical cantilever sensors: material characterization, device development and application in explosive vapour detection. Nanotechnology, 2011, 22, 295501.	1.3	110
4	$1/f$ Noise in Drain and Gate Current of MOSFETs With High- k Gate Stacks. IEEE Transactions on Device and Materials Reliability, 2009, 9, 180-189.	1.5	107
5	Insights Into the Design and Optimization of Tunnel-FET Devices and Circuits. IEEE Transactions on Electron Devices, 2011, 58, 1045-1053.	1.6	100
6	Physical Insight Toward Heat Transport and an Improved Electrothermal Modeling Framework for FinFET Architectures. IEEE Transactions on Electron Devices, 2012, 59, 1353-1363.	1.6	90
7	DC Compact Model for SOI Tunnel Field-Effect Transistors. IEEE Transactions on Electron Devices, 2012, 59, 2635-2642.	1.6	88
8	Impact of Halo Doping on the Subthreshold Performance of Deep-Submicrometer CMOS Devices and Circuits for Ultralow Power Analog/Mixed-Signal Applications. IEEE Transactions on Electron Devices, 2007, 54, 241-248.	1.6	87
9	NBTI Degradation and Its Impact for Analog Circuit Reliability. IEEE Transactions on Electron Devices, 2005, 52, 2609-2615.	1.6	85
10	Impact of High- k Gate Dielectrics on the Device and Circuit Performance of Nanoscale FinFETs. IEEE Electron Device Letters, 2007, 28, 295-297.	2.2	85
11	The effect of high-K gate dielectrics on deep submicrometer CMOS device and circuit performance. IEEE Transactions on Electron Devices, 2002, 49, 826-831.	1.6	78
12	Silanization and antibody immobilization on SU-8. Applied Surface Science, 2007, 253, 3127-3132.	3.1	74
13	An ultra-sensitive piezoresistive polymer nano-composite microcantilever sensor electronic nose platform for explosive vapor detection. Sensors and Actuators B: Chemical, 2014, 192, 444-451.	4.0	72
14	A novel dry method for surface modification of SU-8 for immobilization of biomolecules in Bio-MEMS. Biosensors and Bioelectronics, 2007, 22, 2429-2435.	5.3	69
15	Microscopic Origin of Piezoelectricity in Lead-Free Halide Perovskite: Application in Nanogenerator Design. ACS Energy Letters, 2019, 4, 1004-1011.	8.8	65
16	Polymer microcantilever biochemical sensors with integrated polymer composites for electrical detection. Solid State Sciences, 2009, 11, 1606-1611.	1.5	64
17	Modeling of parasitic capacitances in deep submicrometer conventional and high-K dielectric MOS transistors. IEEE Transactions on Electron Devices, 2003, 50, 959-966.	1.6	62
18	Sub-20 nm gate length FinFET design: Can high- k spacers make a difference?. , 2008, , .		60

#	ARTICLE	IF	CITATIONS
19	Fluorescence and Piezoresistive Cantilever Sensing of Trinitrotoluene by an Upper-Rim Tetrabenzimidazole Conjugate of Calix[4]arene and Delineation of the Features of the Complex by Molecular Dynamics. <i>ACS Applied Materials & Interfaces</i> , 2013, 5, 13448-13456.	4.0	60
20	Giant UV Photoresponse of GaN-Based Photodetectors by Surface Modification Using Phenol-Functionalized Porphyrin Organic Molecules. <i>ACS Applied Materials & Interfaces</i> , 2019, 11, 12017-12026.	4.0	59
21	Vocal Melody Extraction in the Presence of Pitched Accompaniment in Polyphonic Music. <i>IEEE Transactions on Audio Speech and Language Processing</i> , 2010, 18, 2145-2154.	3.8	58
22	OFET based explosive sensors using diketopyrrolopyrrole and metal organic framework composite active channel material. <i>Sensors and Actuators B: Chemical</i> , 2016, 223, 114-122.	4.0	58
23	Photopatternable nano-composite (SU-8/ZnO) thin films for piezo-electric applications. <i>Applied Physics Letters</i> , 2012, 101, .	1.5	56
24	Device scaling effects on hot-carrier induced interface and oxide-trapped charge distributions in MOSFETs. <i>IEEE Transactions on Electron Devices</i> , 2000, 47, 789-796.	1.6	53
25	Device Design and Optimization Considerations for Bulk FinFETs. <i>IEEE Transactions on Electron Devices</i> , 2008, 55, 609-615.	1.6	53
26	Flicker noise in GaN/Al/sub 0.15/Ga/sub 0.85/N doped channel heterostructure field effect transistors. <i>IEEE Electron Device Letters</i> , 1998, 19, 475-477.	2.2	50
27	Polymer composite-based OFET sensor with improved sensitivity towards nitro based explosive vapors. <i>Sensors and Actuators B: Chemical</i> , 2010, 148, 158-165.	4.0	50
28	Fabrication and Characterization of a Polymeric Microcantilever With an Encapsulated Hotwire CVD Polysilicon Piezoresistor. <i>Journal of Microelectromechanical Systems</i> , 2009, 18, 79-87.	1.7	49
29	Part I: Mixed-Signal Performance of Various High-Voltage Drain-Extended MOS Devices. <i>IEEE Transactions on Electron Devices</i> , 2010, 57, 448-457.	1.6	48
30	Optimization and realization of sub-100-nm channel length single halo p-MOSFETs. <i>IEEE Transactions on Electron Devices</i> , 2002, 49, 1077-1079.	1.6	47
31	A Novel Photoplastic Piezoelectric Nanocomposite for MEMS Applications. <i>Journal of Microelectromechanical Systems</i> , 2012, 21, 259-261.	1.7	46
32	Explosive vapor sensor using poly (3-hexylthiophene) and CuII tetraphenylporphyrin composite based organic field effect transistors. <i>Applied Physics Letters</i> , 2008, 93, .	1.5	44
33	Strain induced anisotropic effect on electron mobility in C60 based organic field effect transistors. <i>Applied Physics Letters</i> , 2012, 101, 083305.	1.5	44
34	Impact of lateral asymmetric channel doping on deep submicrometer mixed-signal device and circuit performance. <i>IEEE Transactions on Electron Devices</i> , 2003, 50, 2481-2489.	1.6	43
35	Solution-Processed n-Type Organic Field-Effect Transistors With High on /off Current Ratios Based on Fullerene Derivatives. <i>IEEE Electron Device Letters</i> , 2007, 28, 880-883.	2.2	43
36	Al-doped ZnO thin-film transistor embedded micro-cantilever as a piezoresistive sensor. <i>Applied Physics Letters</i> , 2013, 102, .	1.5	43

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37	Toward System on Chip (SoC) Development Using FinFET Technology: Challenges, Solutions, Process Co-Development & Optimization Guidelines. IEEE Transactions on Electron Devices, 2011, 58, 1597-1607.	1.6	42
38	Solution-Processed Bootstrapped Organic Inverters Based on P3HT With a High- κ Gate Dielectric Material. IEEE Electron Device Letters, 2009, 30, 484-486.	2.2	40
39	Determining ionizing radiation using sensors based on organic semiconducting material. Applied Physics Letters, 2009, 94, 123304.	1.5	39
40	A Novel Bottom Spacer FinFET Structure for Improved Short-Channel, Power-Delay, and Thermal Performance. IEEE Transactions on Electron Devices, 2010, 57, 1287-1294.	1.6	38
41	An ultra-sensitive piezoresistive polymer nano-composite microcantilever platform for humidity and soil moisture detection. Sensors and Actuators B: Chemical, 2014, 203, 165-173.	4.0	38
42	The Effect of LAC Doping on Deep Submicrometer Transistor Capacitances and its Influence on Device RF Performance. IEEE Transactions on Electron Devices, 2004, 51, 1416-1423.	1.6	36
43	A Novel and Robust Approach for Common Mode Feedback Using IDDG FinFET. IEEE Transactions on Electron Devices, 2008, 55, 3274-3282.	1.6	36
44	Exploration of velocity overshoot in a high-performance deep sub-0.1- μ m SOI MOSFET with asymmetric channel profile. IEEE Electron Device Letters, 1999, 20, 538-540.	2.2	35
45	A Roadmap for Disruptive Applications and Heterogeneous Integration Using Two-Dimensional Materials: State-of-the-Art and Technological Challenges. Nano Letters, 2021, 21, 6359-6381.	4.5	35
46	A comprehensive study of hot-carrier induced interface and oxide trap distributions in MOSFETs using a novel charge pumping technique. IEEE Transactions on Electron Devices, 2000, 47, 171-177.	1.6	34
47	Vibrational energy harvesting using photo-patternable piezoelectric nanocomposite cantilevers. Nano Energy, 2013, 2, 923-932.	8.2	33
48	Power-area evaluation of various double-gate RF mixer topologies. IEEE Electron Device Letters, 2005, 26, 664-666.	2.2	32
49	A Novel Table-Based Approach for Design of FinFET Circuits. IEEE Transactions on Computer-Aided Design of Integrated Circuits and Systems, 2009, 28, 1061-1070.	1.9	32
50	Sub 0.5 V Operation of Performance Driven Mobile Systems Based on Area Scaled Tunnel FET Devices. IEEE Transactions on Electron Devices, 2013, 60, 2626-2633.	1.6	31
51	Zinc oxide nanorods functionalized paper for protein preconcentration in biodiagnostics. Scientific Reports, 2017, 7, 43905.	1.6	31
52	Part II: On the Three-Dimensional Filamentation and Failure Modeling of STI Type DeNMOS Device Under Various ESD Conditions. IEEE Transactions on Electron Devices, 2010, 57, 2243-2250.	1.6	30
53	Piezoresistive SU-8 Cantilever With Fe(III)Porphyrin Coating for CO Sensing. IEEE Nanotechnology Magazine, 2012, 11, 701-706.	1.1	30
54	A Novel Drain-Extended FinFET Device for High-Voltage High-Speed Applications. IEEE Electron Device Letters, 2012, 33, 1432-1434.	2.2	30

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55	“Organic CanteFET” A Nanomechanical Polymer Cantilever Sensor With Integrated OFET. Journal of Microelectromechanical Systems, 2012, 21, 294-301.	1.7	30
56	Organic FETs with HWCVD silicon nitride as a passivation layer and gate dielectric. Thin Solid Films, 2008, 516, 770-772.	0.8	29
57	A Binary Tunnel Field Effect Transistor with a Steep Sub-threshold Swing and Increased ON Current. Japanese Journal of Applied Physics, 2010, 49, 120203.	0.8	29
58	PVA modified ZnO nanowire based microsensors platform for relative humidity and soil moisture measurement. Sensors and Actuators B: Chemical, 2017, 253, 1071-1078.	4.0	28
59	A Novel TCAD-Based Thermal Extraction Approach for Nanoscale FinFETs. IEEE Transactions on Electron Devices, 2017, 64, 1404-1407.	1.6	27
60	Monitoring soil pH variation using Polyaniline/SU-8 composite film based conductometric microsensor. Sensors and Actuators B: Chemical, 2019, 286, 583-590.	4.0	27
61	Impact of Fringe Capacitance on the Performance of Nanoscale FinFETs. IEEE Electron Device Letters, 2010, 31, 83-85.	2.2	26
62	H2S detection using low-cost SnO2 nano-particle Bi-layer OFETs. Sensors and Actuators B: Chemical, 2016, 235, 378-385.	4.0	26
63	Part I: High-Voltage MOS Device Design for Improved Static and RF Performance. IEEE Transactions on Electron Devices, 2015, 62, 3168-3175.	1.6	25
64	E-Nose: Multichannel Analog Signal Conditioning Circuit With Pattern Recognition for Explosive Sensing. IEEE Sensors Journal, 2020, 20, 1373-1382.	2.4	25
65	Polymeric Piezoresistive Microcantilevers With Reduced Electrical Variability. Journal of Microelectromechanical Systems, 2015, 24, 1111-1116.	1.7	24
66	Significant improvement in the electrical characteristics of Schottky barrier diodes on molecularly modified Gallium Nitride surfaces. Applied Physics Letters, 2018, 112, .	1.5	24
67	A direct charge pumping technique for spatial profiling of hot-carrier induced interface and oxide traps in MOSFETs. Solid-State Electronics, 1999, 43, 915-922.	0.8	23
68	Part II: Investigation of Subthreshold Swing in Line Tunnel FETs Using Bias Stress Measurements. IEEE Transactions on Electron Devices, 2013, 60, 4065-4072.	1.6	22
69	Investigation of effects of ionizing radiation exposure on material properties of organic semiconducting oligomer “ Pentacene. Organic Electronics, 2013, 14, 1467-1476.	1.4	22
70	Development of graphene nanoplatelet embedded polymer microcantilever for vapour phase explosive detection applications. Journal of Applied Physics, 2014, 116, 124902.	1.1	22
71	Low temperature silicon nitride deposited by Cat-CVD for deep sub-micron metal“oxide“ semiconductor devices. Thin Solid Films, 2001, 395, 270-274.	0.8	21
72	Rare Earth Oxides in Microelectronics. , 0, , 345-365.		21

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73	Understanding and Optimization of Hot-Carrier Reliability in Germanium-on-Silicon pMOSFETs. IEEE Transactions on Electron Devices, 2009, 56, 1063-1069.	1.6	21
74	Part I: On the Behavior of STI-Type DeNMOS Device Under ESD Conditions. IEEE Transactions on Electron Devices, 2010, 57, 2235-2242.	1.6	21
75	Electret mechanism, hysteresis, and ambient performance of sol-gel silica gate dielectrics in pentacene field-effect transistors. Applied Physics Letters, 2007, 91, .	1.5	20
76	Electrical actuation and readout in a nanoelectromechanical resonator based on a laterally suspended zinc oxide nanowire. Nanotechnology, 2012, 23, 025501.	1.3	20
77	A novel piezoresistive polymer nanocomposite MEMS accelerometer. Journal of Micromechanics and Microengineering, 2017, 27, 015014.	1.5	20
78	Low-Operating-Voltage Operation and Improvement in Sensitivity With Passivated OFET Sensors for Determining Total Dose Radiation. IEEE Electron Device Letters, 2010, 31, 1482-1484.	2.2	19
79	Facile fabrication of graphene devices through metalloporphyrin induced photocatalytic reduction. RSC Advances, 2012, 2, 4120.	1.7	19
80	Local piezoelectric response of ZnO nanoparticles embedded in a photosensitive polymer. Physica Status Solidi - Rapid Research Letters, 2012, 6, 77-79.	1.2	19
81	Current Excitation Method for ΔR Measurement in Piezo-Resistive Sensors With a 0.3-ppm Resolution. IEEE Transactions on Instrumentation and Measurement, 2012, 61, 767-774.	2.4	19
82	Copper(II) phthalocyanine based organic electronic devices for ionizing radiation dosimetry applications. Organic Electronics, 2013, 14, 1281-1290.	1.4	19
83	A new oxide trap-assisted NBTI degradation model. IEEE Electron Device Letters, 2005, 26, 687-689.	2.2	18
84	Design and Fabrication Issues in Affinity Cantilevers for bioMEMS Applications. Journal of Microelectromechanical Systems, 2006, 15, 1789-1794.	1.7	18
85	Drain Current Model Including Velocity Saturation for Symmetric Double-Gate MOSFETs. IEEE Transactions on Electron Devices, 2008, 55, 2173-2180.	1.6	17
86	On the dc and noise properties of the gate current in epitaxial Ge p-channel metal oxide semiconductor field effect transistors with TiN-TaN-HfO ₂ -SiO ₂ gate stack. Applied Physics Letters, 2008, 92, .	1.5	17
87	A novel architecture for improving slew rate in FinFET-based op-amps and OTAs. Microelectronics Journal, 2011, 42, 758-765.	1.1	17
88	Low cost fabrication of polymer composite (h-ZnO + PDMS) material for piezoelectric device application. Materials Research Express, 2016, 3, 075702.	0.8	17
89	Superior hot carrier reliability of single halo (SH) silicon-on-insulator (SOI) nMOSFET in analog applications. IEEE Transactions on Device and Materials Reliability, 2005, 5, 127-132.	1.5	16
90	Implications of fin width scaling on variability and reliability of high-k metal gate FinFETs. Microelectronic Engineering, 2010, 87, 1963-1967.	1.1	16

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91	Variable Interface Dipoles of Metallated Porphyrin Self-Assembled Monolayers for Metal-Gate Work Function Tuning in Advanced CMOS Technologies. IEEE Nanotechnology Magazine, 2010, 9, 335-337.	1.1	16
92	ZnO Nanowire Embedded Strain Sensing Cantilever: A New Ultra-Sensitive Technology Platform. Journal of Microelectromechanical Systems, 2013, 22, 995-997.	1.7	16
93	Low Cost, Large Area, Flexible Graphene Nanocomposite Films for Energy Harvesting Applications. IEEE Nanotechnology Magazine, 2017, 16, 259-264.	1.1	16
94	Detection of heart-type fatty acid-binding protein (h-FABP) using piezoresistive polymer microcantilevers functionalized by a dry method. Applied Nanoscience (Switzerland), 2018, 8, 1031-1042.	1.6	16
95	Analysis of floating body effects in thin film conventional and single pocket SOI MOSFETs using the GIDL current technique. IEEE Electron Device Letters, 2002, 23, 209-211.	2.2	15
96	A new method to characterize border traps in submicron transistors using hysteresis in the drain current. IEEE Transactions on Electron Devices, 2003, 50, 973-979.	1.6	15
97	Investigations of enhanced device characteristics in pentacene-based field effect transistors with sol-gel interfacial layer. Applied Physics Letters, 2007, 90, 122112.	1.5	15
98	Part II: A Novel Scheme to Optimize the Mixed-Signal Performance and Hot-carrier Reliability of Drain-Extended MOS Devices. IEEE Transactions on Electron Devices, 2010, 57, 458-465.	1.6	15
99	Poly(3-hexylthiophene) and hexafluoro-2-propanol-substituted polysiloxane based OFETs as a sensor for explosive vapor detection. Sensors and Actuators A: Physical, 2011, 171, 12-18.	2.0	15
100	Modeling, Simulation, and Design Guidelines for Piezoresistive Affinity Cantilevers. Journal of Microelectromechanical Systems, 2011, 20, 774-784.	1.7	15
101	Porphyrim Self-Assembled Monolayer as a Copper Diffusion Barrier for Advanced CMOS Technologies. IEEE Transactions on Electron Devices, 2012, 59, 1963-1969.	1.6	15
102	Detection of the Chilli Leaf Curl Virus Using an Attenuated Total Reflection-Mediated Localized Surface-Plasmon-Resonance-Based Optical Platform. ACS Omega, 2021, 6, 17413-17423.	1.6	15
103	Fabrication and characterization of novel polymer composite microcantilever sensors for explosive detection. , 2010, , .		14
104	Mobility enhancement of solution-processed Poly(3-Hexylthiophene) based organic transistor using zinc oxide nanostructures. Composites Part B: Engineering, 2012, 43, 1645-1648.	5.9	14
105	Morphology and Curie temperature engineering in crystalline La _{0.7} Sr _{0.3} MnO ₃ films on Si by pulsed laser deposition. Journal of Applied Physics, 2014, 115, .	1.1	14
106	Benchmarking the device performance at sub 22 nm node technologies using an SoC framework. , 2009, , .		13
107	Fabrication of Unipolar Graphene Field-Effect Transistors by Modifying Source and Drain Electrode Interfaces with Zinc Porphyrin. ACS Applied Materials & Interfaces, 2012, 4, 1434-1439.	4.0	13
108	Comparison among different algorithms in classifying explosives using OFETs. Sensors and Actuators B: Chemical, 2013, 176, 46-51.	4.0	13

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109	A Vapor Phase Self-Assembly of Porphyrin Monolayer as a Copper Diffusion Barrier for Back-End-of-Line CMOS Technologies. IEEE Transactions on Electron Devices, 2016, 63, 2009-2015.	1.6	13
110	Asymmetric immobilization of antibodies on a piezo-resistive micro-cantilever surface. RSC Advances, 2016, 6, 17606-17616.	1.7	13
111	Ultra-sensitive gas phase detection of 2,4,6-trinitrotoluene by non-covalently functionalized graphene field effect transistors. Analyst, The, 2020, 145, 917-928.	1.7	13
112	A study of hot-carrier induced interface-trap profiles in lateral asymmetric channel MOSFETs using a novel charge pumping technique. Solid-State Electronics, 2001, 45, 1717-1723.	0.8	12
113	Performance and hot-carrier reliability of 100 nm channel length jet vapor deposited Si/sub 3/N/sub 4/ MNSFETs. IEEE Transactions on Electron Devices, 2001, 48, 679-684.	1.6	12
114	On the failure mechanism and current instabilities in RESURF type DeNMOS device under ESD conditions. , 2010, , .		12
115	Negative differential conductivity and carrier heating in gate-all-around Si nanowire FETs and its impact on CMOS logic circuits. Japanese Journal of Applied Physics, 2014, 53, 04EC16.	0.8	12
116	Role of Injection Barrier in Capacitance-Voltage Measurements of Organic Devices. IEEE Electron Device Letters, 2014, 35, 581-583.	2.2	12
117	Piezoresistive microcantilever based lab-on-a-chip system for detection of macronutrients in the soil. Solid-State Electronics, 2017, 138, 94-100.	0.8	12
118	Microcantilever Based Dual Mode Biosensor for Agricultural Applications. IEEE Sensors Journal, 2020, 20, 6826-6832.	2.4	12
119	High-field stressing of LPCVD gate oxides. IEEE Electron Device Letters, 1997, 18, 84-86.	2.2	11
120	A study of 100 nm channel length asymmetric channel MOSFET by using charge pumping. Microelectronic Engineering, 1999, 48, 193-196.	1.1	11
121	Border-Trap Characterization in High- κ Strained-Si MOSFETs. IEEE Electron Device Letters, 2007, 28, 731-733.	2.2	11
122	A novel technique for microfabrication of ultra-thin affinity cantilevers for characterization with an AFM. Journal of Micromechanics and Microengineering, 2010, 20, 125007.	1.5	11
123	3D TCAD based approach for the evaluation of nanoscale devices during ESD failure. , 2010, , .		11
124	Insight into the charge transport and degradation mechanisms in organic transistors operating at elevated temperatures in air. Organic Electronics, 2015, 22, 202-209.	1.4	11
125	A Novel PET-Based Piezoresistive MEMS Sensor Platform for Agricultural Applications. Journal of Microelectromechanical Systems, 2017, 26, 746-748.	1.7	11
126	Sensitivity Improvement of Medical Dosimeters Using Solution Processed TIPS-Pentacene FETs. IEEE Sensors Journal, 2019, 19, 4428-4434.	2.4	11

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127	Sub-50-mV Nanoelectromechanical Switch Without Body Bias. IEEE Transactions on Electron Devices, 2020, 67, 3894-3897.	1.6	11
128	A Passive Gamma Radiation Dosimeter Using Graphene Field Effect Transistor. IEEE Sensors Journal, 2020, 20, 2938-2944.	2.4	11
129	Hybrid Pattern Recognition for Rapid Explosive Sensing With Comprehensive Analysis. IEEE Sensors Journal, 2021, 21, 8011-8019.	2.4	11
130	100 nm channel length MNSFETs using a jet vapor deposited ultra-thin silicon nitride gate dielectric. , 0, , .		10
131	CHISEL programming operation of scaled nor flash EEPROMs-effect of voltage scaling, device scaling and technological parameters. IEEE Transactions on Electron Devices, 2003, 50, 2104-2111.	1.6	10
132	Preparation, Characterization, and Electrical Properties of a Self-Assembled meso-Pyridyl Porphyrin Monolayer on Gold Surfaces. Australian Journal of Chemistry, 2005, 58, 810.	0.5	10
133	Metallated Porphyrin Self Assembled Monolayers as Cu Diffusion Barriers for the Nano-Scale CMOS Technologies. , 2008, , .		10
134	A new physical insight and 3D device modeling of STI type denmos device failure under ESD conditions. , 2009, , .		10
135	A Spectroscopy and Microscopy Study of Parylene-C OFETs for Explosive Sensing. IEEE Sensors Journal, 2018, 18, 1364-1372.	2.4	10
136	Highly conducting doped poly-Si deposited by hot wire CVD and its applicability as gate material for CMOS devices. Thin Solid Films, 2003, 430, 63-66.	0.8	9
137	Evaluation of the Impact of Layout on Device and Analog Circuit Performance With Lateral Asymmetric Channel MOSFETs. IEEE Transactions on Electron Devices, 2005, 52, 1603-1609.	1.6	9
138	Drain current model for nanoscale double-gate MOSFETs. Solid-State Electronics, 2009, 53, 1001-1008.	0.8	9
139	NANOMECHANICAL CHARACTERIZATION OF MULTIFERROIC THIN FILMS FOR MICRO-ELECTROMECHANICAL SYSTEMS. International Journal of Nanoscience, 2011, 10, 1039-1043.	0.4	9
140	Lanthanide complexes as molecular dopants for realizing air-stable n-type graphene logic inverters with symmetric transconductance. Materials Horizons, 2019, 6, 743-750.	6.4	9
141	Enhanced Performance of MSM UV Photodetectors by Molecular Modification of Gallium Nitride Using Porphyrin Organic Molecules. IEEE Transactions on Electron Devices, 2019, 66, 2036-2039.	1.6	9
142	Passivation of Solution-Processed a-IGZO Thin-Film Transistor by Solution Processable Zinc Porphyrin Self-Assembled Monolayer. IEEE Transactions on Electron Devices, 2021, 68, 5920-5924.	1.6	9
143	Hysteresis behavior in 85-nm channel length vertical n-MOSFETs grown by MBE. IEEE Transactions on Electron Devices, 1996, 43, 973-976.	1.6	8
144	Highly resistive body STI NDeMOS: An optimized DeMOS device to achieve moving current filaments for robust ESD protection. , 2009, , .		8

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145	A Solution Toward the OFF-State Degradation in Drain-Extended MOS Device. IEEE Transactions on Electron Devices, 2010, 57, 3536-3539.	1.6	8
146	PHOTOPLASTIC MICROCANTILEVER SENSOR PLATFORM FOR EXPLOSIVE DETECTION. International Journal of Nanoscience, 2011, 10, 739-743.	0.4	8
147	Solution processed photopatternable high-k nanocomposite gate dielectric for low voltage organic field effect transistors. Microelectronic Engineering, 2012, 96, 92-95.	1.1	8
148	Fabrication, Characterization and Application of ZnO Nanostructure-Based Micro-Preconcentrator for TNT Sensing. Journal of Microelectromechanical Systems, 2016, 25, 968-975.	1.7	8
149	Polymer-Based Micro/Nano Cantilever Electro-Mechanical Sensor Systems for Bio/Chemical Sensing Applications. Springer Tracts in Mechanical Engineering, 2014, , 403-422.	0.1	8
150	Radiation-induced interface state generation in reoxidized nitrided SiO ₂ . Journal of Applied Physics, 1992, 71, 1029-1031.	1.1	7
151	Characterization of lateral asymmetric channel (LAC) thin film SOI MOSFETs. , 0, , .		7
152	The Effect of Single-Halo Doping on the Low-Frequency Noise Performance of Deep Submicrometer MOSFETs. IEEE Electron Device Letters, 2006, 27, 995-997.	2.2	7
153	Device optimization of bulk FinFETs and its comparison with SOI FinFETs. , 2007, , .		7
154	Spin-coatable, photopatternable magnetic nanocomposite thin films for MEMS device applications. RSC Advances, 2015, 5, 85741-85747.	1.7	7
155	A Nano-Electro-Mechanical Switch Based Power Gating for Effective Stand-by Power Reduction in FinFET Technologies. IEEE Electron Device Letters, 2017, 38, 681-684.	2.2	7
156	Pentacene Organic Field Effect Transistors on Flexible substrates with polymer dielectrics. , 2007, , .		6
157	Filament study of STI type drain extended NMOS device using transient interferometric mapping. , 2009, , .		6
158	On the thermal failure in nanoscale devices: Insight towards heat transport including critical BEOL and design guidelines for robust thermal management & EOS/ESD reliability. , 2011, , .		6
159	Anomalous Width Dependence of Gate Current in High- κ Metal Gate nMOS Transistors. IEEE Electron Device Letters, 2015, 36, 739-741.	2.2	6
160	PBTI in HKMG nMOS Transistors Effect of Width, Layout, and Other Technological Parameters. IEEE Transactions on Electron Devices, 2017, 64, 4018-4024.	1.6	6
161	Microcantilever Based Dual Mode Optical Biosensor for Agricultural Pathogen Detection. , 2018, , .		6
162	Non-Volatile Organic Transistor Memory Based on Black Phosphorus Quantum Dots as Charge Trapping Layer. IEEE Electron Device Letters, 2020, 41, 852-855.	2.2	6

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163	Piezoresistance in ballistic graphene. Physical Review Materials, 2019, 3, .	0.9	6
164	Charge injection using gate-induced-drain-leakage current for characterization of plasma edge damage in CMOS devices. IEEE Transactions on Semiconductor Manufacturing, 1998, 11, 211-216.	1.4	5
165	Ultra-thin silicon nitride by hot wire chemical vapor deposition (HWCVD) for deep sub-micron CMOS technologies. Microelectronic Engineering, 2002, 61-62, 625-629.	1.1	5
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